

REMARKS

Claim 200 has been amended. Claims 124-137, 170-188, and 200-209 are pending. Claims 124-137 and 170-188 are withdrawn from consideration. The Title of the Invention has been amended to correspond more closely to the pending claims. Applicant reserves the right to pursue the original claims and other claims in this and other applications. Please reconsider the above-referenced application in light of the foregoing amendment and following remarks.

Claims 200-204 and 209 stand rejected under 35 U.S.C. § 102(b) as being anticipated by U.S. patent no. 5,488,010 ("Wong"). The rejection is respectfully traversed.

At the outset, Applicant notes that claims 205-208 are not rejected in the present Office Action, and are believed to be in immediate condition for allowance. Claim 200 has been amended to recite a method of forming a photosensor comprising, "excavating a trench within a semiconductor substrate, said trench having a substantially vertical internal surface region and bottom surface region; performing a first ion implantation into said substantially vertical internal surface region and bottom surface region at a first ion implantation angle; performing a second ion implantation into said substantially vertical internal surface region and bottom surface region at a second ion implantation angle."

Wong does not disclose performing a first ion implantation into the vertical internal surface region *and* bottom surface region, much less a second ion implantation into the vertical internal surface region *and* bottom surface region. In fact, Wong teaches away from such a method. Wong discloses that "[i]f a buried channel is desired on the sidewall of the CCD, a large tilt angle implant may be performed twice, *once on each side* of the trench." (Col. 7, lines 10-14) (emphasis added). In contrast, Applicant's

disclosed method implants the sidewall *and* the bottom of the trench.

Claims 201-209 depend from claim 200 and should be similarly allowable along with claim 200 for at least the reasons provided above. Moreover, Wong does not disclose that the "first implantation angle is *orthogonal* to said second ion implantation angle," as recited in dependent claim 201 (emphasis added). This is an additional reason for the allowance of claim 201.

In view of the above, each of the presently pending claims in this application is believed to be in immediate condition for allowance. Accordingly, the Examiner is respectfully requested to review and pass this application to issue.

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Respectfully submitted,

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